# **2SB0643, 2SB0644** (2SB643, 2SB644)

## Silicon PNP epitaxial planar type

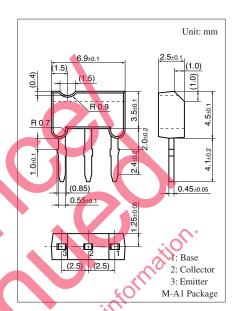
## For low-frequency general amplification

#### ■ Features

• M type package allowing easy automatic and manual insertion as well as stand-alone fixing to the printed circuit board.

## ■ Absolute Maximum Ratings $T_a = 25$ °C

Parameter	Symbol	Rating	Unit	
Collector-base voltage	2SB0643	V <sub>CBO</sub>	-30	V
(Emitter open)	2SB0644		-60	
Collector-emitter voltage	2SB0643	V <sub>CEO</sub>	-25	V
(Base open)	2SB0644		-50	
Emitter-base voltage (Coll	V <sub>EBO</sub>	-7	V	
Collector current	$I_C$	- 0.5	A	
Peak collector current	$I_{CP}$	-1	A	
Collector power dissipation	Pc	600	mW	
Junction temperature	T <sub>j</sub>	150	°C	
Storage temperature	T <sub>stg</sub>	-55 to +150	°C	



## ■ Electrical Characteristics $T_a = 25^{\circ}C \pm 3^{\circ}C$

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Collector-base voltage 2SB0643	V <sub>CBO</sub>	$I_{\rm C} = -10  \mu A,  I_{\rm E} = 0$	-30			V
(Emitter open) 2SB0644			-60			
Collector-emitter voltage 2SB0643	V <sub>CEO</sub>	$I_C = -2 \text{ mA}, I_R = 0$	-25			V
(Base open) 2SB0644		104/100	-50			
Emitter-base voltage (Collector open)	V <sub>EBO</sub>	$I_{\rm E} = 10  \mu A$ , $I_{\rm C} = 0$	-7			V
Collector-base cutoff current (Emitter open)	$I_{CBO}$	$V_{CB} = -20 \text{ V}, I_E = 0$			- 0.1	μΑ
Collector-Emitter cutoff current (Base open)	I <sub>CEQ</sub>	$V_{CE} = -20 \text{ V}, I_B = 0$			-1	μΑ
Forward current transfer ratio *1	h <sub>FE1</sub> *2	$V_{CE} = -10 \text{ V}, I_{C} = -10 \text{ mA}$	85		340	_
	h <sub>FE2</sub>	$V_{CE} = -10 \text{ V}, I_{C} = -500 \text{ mA}$	40	90		
Collector-emitter saturation voltage	V <sub>CE(sat)</sub>	$I_C = -300 \text{ mA}, I_B = -30 \text{ mA}$		- 0.35	- 0.6	V
Transition frequency	$f_T$	$V_{CB} = -10 \text{ V}, I_E = 10 \text{ mA}, f = 200 \text{ MHz}$		200		MHz
Collector output capacitance	C <sub>ob</sub>	$V_{CB} = -10 \text{ V}, I_E = 0, f = 1 \text{ MHz}$		6	15	pF
(Common base, input open circuited)						

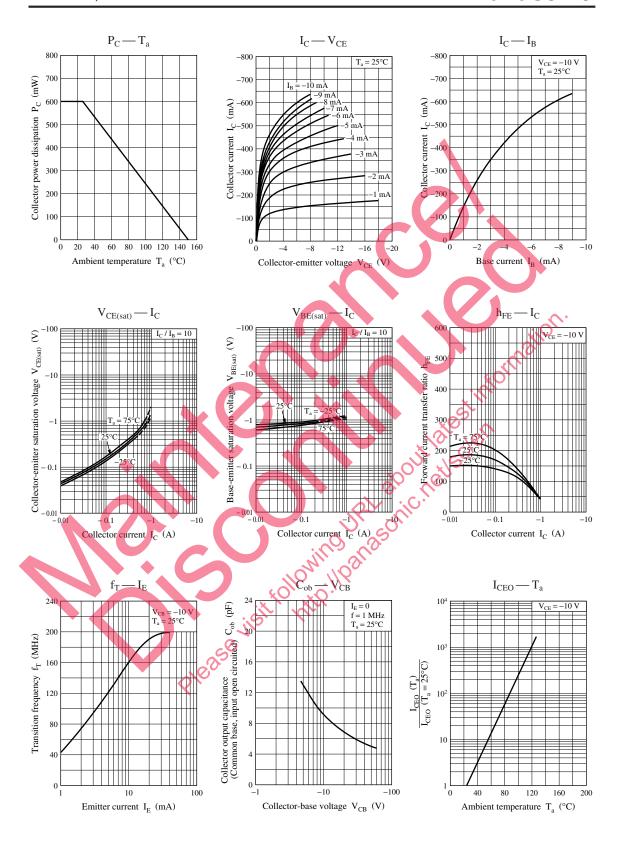
Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

#### 2. \*1: Pulse measurement

#### \*2: Rank classification

Rank	Q	R	S	
$h_{\rm FE1}$	85 to 170	120 to 240	170 to 340	

Note) The part numbers in the parenthesis show conventional part number.



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